SPICE Model Parameters

Please copy this code from the SPICE model into LTSPICE (version 4) software for simulation of the GB20SHT06-CAL.

```
*      MODEL OF GeneSiC Semiconductor Inc.
*
*      $Revision:   1.0            $
*      $Date:   05-SEP-2013        $
*
*      GeneSiC Semiconductor Inc.
*      43670 Trade Center Place Ste. 155
*      Dulles, VA 20166
*
*      COPYRIGHT (C) 2013 GeneSiC Semiconductor Inc.
*      ALL RIGHTS RESERVED
*
* These models are provided "AS IS, WHERE IS, AND WITH NO WARRANTY
* OF ANY KIND EITHER EXPRESSED OR IMPLIED, INCLUDING BUT NOT LIMITED
* TO ANY IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A
* PARTICULAR PURPOSE."
* Models accurate up to 2 times rated drain current.
*
* Start of GB20SHT06-CAL SPICE Model
*
.SUBCKT GB20SHT06 ANODE KATHODE
D1 ANODE KATHODE GB20SHT06_25C; Call the Schottky Diode Model
D2 ANODE KATHODE GB20SHT06_PIN; Call the PiN Diode Model
.MODEL GB20SHT06_25C D
+ IS       8.46E-17      RS        0.0319
+ N        1             IKF       1000
+ EG       1.2           XTI       3
+ TRS1     0.0038        TRS2      3.00E-05
+ CJO      1.26E-09      VJ        0.438
+ M        1.5278        FC        0.5
+ TT       1.00E-10      BV        650
+ IBV      1.00E-03      VPK       650
+ IAVE     20            TYPE      SiC_Schottky
+ MFG      GeneSiC_Semiconductor
.MODEL GB20SHT06_PIN D
+ IS       2.77E-10      RS        0.086693
+ N        3.3505        IKF       3.67E-06
+ EG       3.23          XTI       -10
+ FC       0.5           TT        0
+ BV       650           IBV       1.00E-03
+ VPK      650           IAVE      20
+ TYPE     SiC_PiN
.ENDS
*
* End of GB20SHT06-CAL SPICE Model
```